

L Number	Hits	Search Text	DB	Time stamp
1	5	(("5482871") or ("5926703") or ("6232163") or ("6352882") or ("6407428")).PN.	USPAT	2004/07/13 18:43
2	11	("4656731"   "4697198"   "4829018"   "4927779"   "5185535"   "5294821"   "5359219"   "5440161"   "5506436"   "5736435"   "5780236").PN.	USPAT	2004/07/13 18:37
3	3	5926703.URPN.	USPAT	2004/07/13 18:39
4	8437	((257/66) or (257/173) or (257/328) or (257/336) or (257/339) or (257/344) or (257/347) or (257/355) or (257/356) or (257/367) or (257/408)).CCLS.	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/13 19:00
5	30909	soi or (silicon near2 insulator)	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/13 19:02
6	5641	buried near2 oxide	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/13 19:02
7	1328	(dop\$3 near2 region) near3 (first and second and third)	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/13 19:12
8	1158168	concentration	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/13 19:03
9	3479	(soi or (silicon near2 insulator)) and (buried near2 oxide)	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/13 19:04
10	45	((soi or (silicon near2 insulator)) and (buried near2 oxide)) and ((dop\$3 near2 region) near3 (first and second and third))	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/13 19:04
11	28	(((soi or (silicon near2 insulator)) and (buried near2 oxide)) and ((dop\$3 near2 region) near3 (first and second and third))) and concentration	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/13 19:04
12	9	(((soi or (silicon near2 insulator)) and (buried near2 oxide)) and ((dop\$3 near2 region) near3 (first and second and third))) and concentration and (((257/66) or (257/173) or (257/328) or (257/336) or (257/339) or (257/344) or (257/347) or (257/355) or (257/356) or (257/367) or (257/408)).CCLS.)	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/13 19:05
13	19	(((soi or (silicon near2 insulator)) and (buried near2 oxide)) and ((dop\$3 near2 region) near3 (first and second and third))) and concentration and (((257/66) or (257/173) or (257/328) or (257/336) or (257/339) or (257/344) or (257/347) or (257/355) or (257/356) or (257/367) or (257/408)).CCLS.))	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/13 19:07

14	26	((soi or (silicon near2 insulator)) and (buried near2 oxide)) and ((dop\$3 near2 region) near3 (first and second and third))) not (((((soi or (silicon near2 insulator)) and (buried near2 oxide)) and ((dop\$3 near2 region) near3 (first and second and third))) and concentration) not (((((soi or (silicon near2 insulator)) and (buried near2 oxide)) and ((dop\$3 near2 region) near3 (first and second and third))) and concentration) and ((257/66) or (257/173) or (257/328) or (257/336) or (257/339) or (257/344) or (257/347) or (257/355) or (257/356) or (257/367) or (257/408)).CCLS.))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/13 19:10
15	9238	bulk near3 substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/13 19:10
16	36	(bulk near3 substrate) near5 "17"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/13 19:11
17	79	(bulk near3 substrate) and ((dop\$3 near2 region) near3 (first and second and third))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/13 19:11
18	1	((dop\$3 near2 region) near3 (first and second and third))near5 bulk near3 substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/13 19:18
19	2	((dop\$3 near2 region) near3 (first and second and third))same bulk near3 substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/13 19:14
20	79	((dop\$3 near2 region) near3 (first and second and third))and bulk near3 substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/13 19:14
21	3	((dop\$3 near2 region) near3 (first and second and third))near5 bulk	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/13 19:20
22	0	(dop\$3 near2 region) near5 (bulk near3 substrate) same (high near3 concentrat\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/13 19:47
23	10	(dop\$3 near2 region) near5 (bulk near3 substrate) and (high near3 concentrat\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/13 19:48
24	7	(bulk near3 substrate) same ((high near3 concentrat\$3) near3 (channel or (channel near2 region)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/13 19:52
25	1738	((high near3 concentrat\$3) near3 (channel or (channel near2 region)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/13 19:53

26	442	((high near3 concentrat\$3) near3 (channel or (channel near2 region))) same dop\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/13 19:53
27	100	((high near3 concentrat\$3) near3 (channel or (channel near2 region))) same dop\$3) and (soi or (silicon near2 insulator))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/13 19:53
28	15	((((high near3 concentrat\$3) near3 (channel or (channel near2 region))) same dop\$3) and (soi or (silicon near2 insulator))) and (bulk near3 substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/13 19:55
29	85	((((high near3 concentrat\$3) near3 (channel or (channel near2 region))) same dop\$3) and (soi or (silicon near2 insulator))) not (((((high near3 concentrat\$3) near3 (channel or (channel near2 region))) same dop\$3) and (soi or (silicon near2 insulator))) and (bulk near3 substrate))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/13 19:55
32	11	5599728.URPN.	USPAT	2004/07/13 19:59
33	23	("4697198"   "4746960"   "4784968"   "4899202"   "4948745"   "4961165"   "4985744"   "4990983"   "5072277"   "5095348"   "5102809"   "5116771"   "5125007"   "5160989"   "5212397"   "5219768"   "5243210"   "5258318"   "5264721"   "5355011"   "5359221"   "5399525"   "5413949").PN.	USPAT	2004/07/13 19:59
34	24	5413949.URPN.	USPAT	2004/07/13 20:02
47	21	("4717683"   "5217910"   "5378650"   "5413949"   "5416033"   "5548143"   "5618740"   "5658811"   "5674760"   "5753556"   "5780328"   "5792699"   "5856225"   "5893740"   "5895954"   "5930642"   "5986314"   "6005285"   "6017808"   "6025238"   "6027978").PN.	USPAT	2004/07/13 20:08